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April 2016

# FPF2172 IntelliMAX™ Advanced Load Management

#### **Features**

- 1.8 to 5.5 V Input Voltage Range
- Controlled Turn-On
- 200 mA Current Limit Option
- Under-Voltage Lockout (UVLO)
- Thermal Shutdown
- <1 µA Shutdown Current</p>
- Fast Current Limit Response Time:
  - 3 µs to Moderate Over Currents
  - 20 ns to Hard Shorts
- Integrated very Low VF Schottky Diode for Reverse Current Blocking
- RoHS Compliant

### **Applications**

- PDAs
- Cell Phones
- GPS Devices
- MP3 Players
- Digital Cameras
- Peripheral Ports
- Hot Swap Supplies

## **Description**

The FPF2172 is a load switch which combines the functionality of the IntelliMAX™ series load switch with a very low forward voltage drop Schottky barrier rectifier. The integrated solution provides full protection to systems and loads which may encounter large current conditions in a very compact MLP 3 x 3 package. This device contains a  $0.125 \Omega$  current-limited P-channel MOSFET which can operate over an input voltage range of 1.8-5.5 V. The Schottky diode acts as a barrier so that no reverse current can flow when the MOSFET is off and the output voltage is higher than the input voltage. Switch control is by a logic input (ON) capable of interfacing directly with low voltage control signals. Each part contains thermal shutdown protection which shuts off the switch to prevent damage to the part when a continuous over-current condition causes excessive heating.

When the switch current reaches the current limit, the part operates in a constant-current mode to prohibit excessive currents from causing damage. If the constant current condition still persists after 10 ms, these parts will shut off the switch and pull the fault signal pin (FLAGB) low. The switch will remain off until the ON pin is cycled. The minimum current limit is 200 mA.

These parts are available in a space-saving 6-lead MLP 3 x 3 package.

# **Ordering Information**

Part Number Current Liming [mA]		Current Limit Blanking Time [ms]	Auto-Restart Time [ms]	ON Pin Activity	Top Mark
FPF2172	200	10	n/a	Active HI	2172

# **Typical Application**

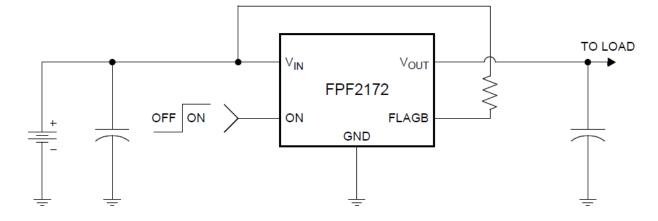


Figure 1. Typical Application

# **Block Diagram**

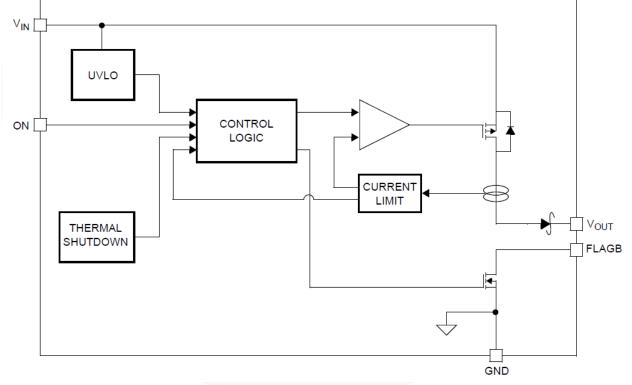


Figure 2. Block Diagram

# **Pin Configuration**

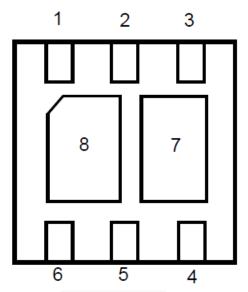


Figure 3. 3 x 3 MLP (Bottom View)

# **Pin Descriptions**

Pin	Name	Description
1	V <sub>IN</sub>	Supply Input. Input to the power switch and the supply voltage for the IC
2, 8	NC	No Connect
3, 7	V <sub>OUT</sub>	Switch Output. Output of the power switch
4	FLAGB	Fault Output. Active LO, open drain output which indicates an over current supply, Under-Voltage or Over-Temperature state.
5	GND	Ground
6	ON	ON Control Input

# **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol		Parameter	Min.	Max.	Unit
V <sub>IN</sub>	V <sub>IN</sub> , ON, FLAGB to GN	ID	-0.3	6.0	V
	V <sub>OUT</sub> to GND	-0.3 20.0		٧	
P <sub>D</sub>	Power Dissipation @ $T_A = 25^{\circ}C^{(1)}$			1.4	W
T <sub>A</sub>	Operating Temperatur	e Range	-40	85	°C
T <sub>STG</sub>	Storage Temperature	torage Temperature			ô
$\Theta_{JA}$	Thermal Resistance, J	nermal Resistance, Junction to Ambient			³C/W
ESD	Electrostatic Discharge Capability	Human Body Model		4000	V
		Machine Model		400	V

#### Note:

1. Package power dissipation on 1 square inch pad, 2 oz. copper board.

### **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

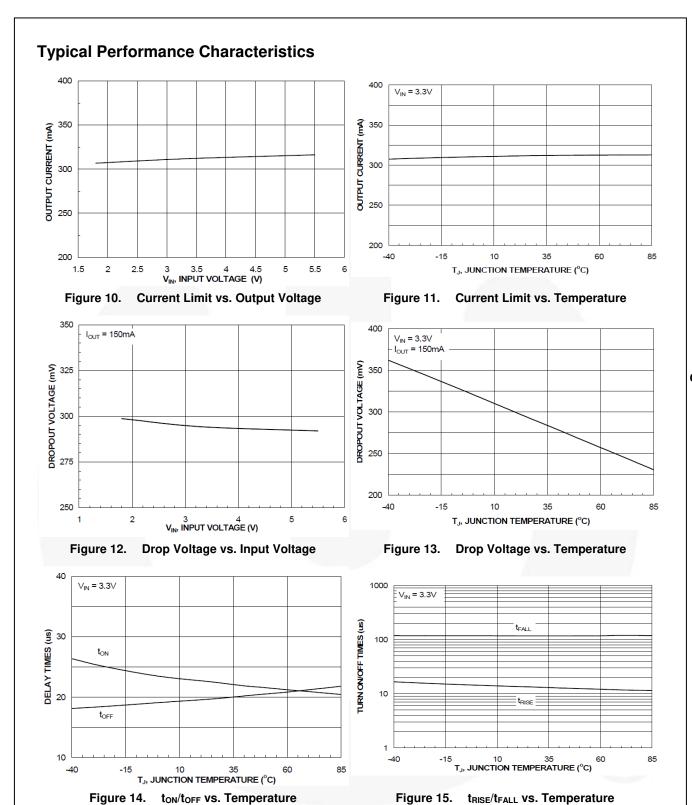
Symbol	Parameter	Min.	Max.	Unit
$V_{IN}$	Input Voltage	1.8	5.5	V
T <sub>A</sub>	Ambient Operating Temperature	-40	85	°C

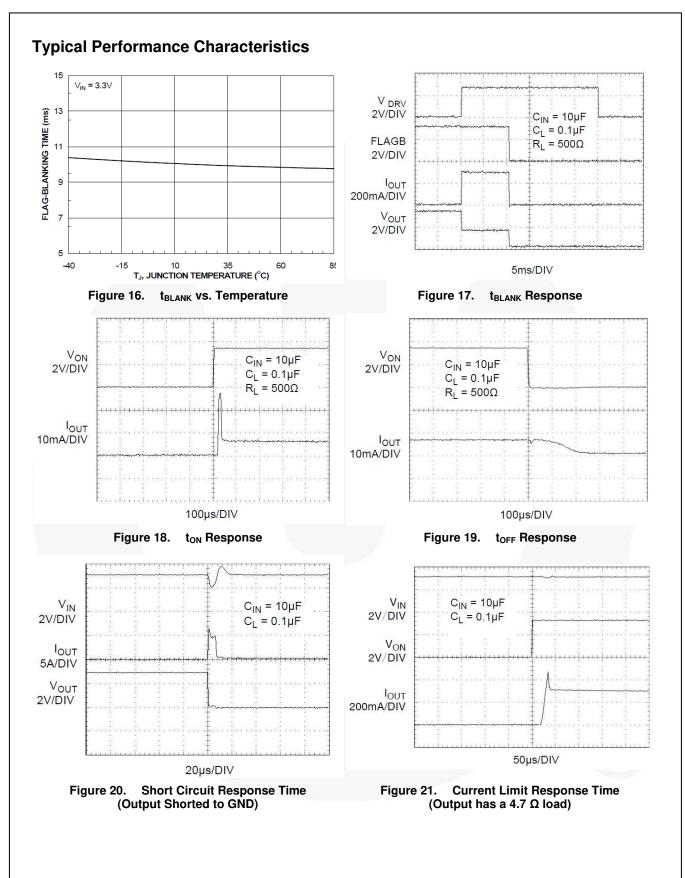
## **Electrical Characteristics**

 $V_{IN}$  = 1.8 to 5.5 V,  $T_A$  = -40 to +85°C unless otherwise noted. Typical values are at  $V_{IN}$  = 3.3 V and  $T_A$  = 25°C.

Symbol	Parameter	Conditions		Min.	Тур.	Max.	Uni	
Basic Oper	ation			•				
$V_{\text{IN}}$	Operating Voltage			1.8		5.5	V	
	Outropy to Comment	I <sub>OUT</sub> =0 mA,	/ <sub>IN</sub> =1.8 V to 3.3 V		95			
lα	Quiescent Current	$V_{ON}$ Active $V_{IN}=3.3 \text{ V to } 5.5 \text{ V}$			110	200	μA	
I <sub>SHDN</sub>	Shutdown Current					1.0	μA	
I <sub>LATCHOFF</sub>	Latch-Off Current	V <sub>ON</sub> =V <sub>IN</sub> , after and O	ver-Current Fault		50		μA	
I <sub>R</sub>	Reverse Block Leakage Current	$V_{OUT} = 20 \text{ V}, V_{IN} = V_{ON} = 0 \text{ V},$ $T_A = 25^{\circ}\text{C}$			10	100	μΑ	
	Reverse Breakdown Voltage	I <sub>OUT</sub> = 250 mA					V	
		T <sub>A</sub> = 25°C, I <sub>OUT</sub> = 150 mA		-1	0.3	0.4	V	
$V_{DROP}$	Dropout Voltage	T <sub>A</sub> = 85°C, I <sub>OUT</sub> = 150 mA			0.23			
		$T_A = -40^{\circ}C, I_{OUT} = 15$	0 mA		0.36		•	
		$V_{IN} = 1.8 \text{ V}$		0.75				
$V_{IH}$	On Input Logic HIGH Voltage	V <sub>IN</sub> = 5.5 V		1.3			V	
.,		V <sub>IN</sub> = 1.8 V				0.5	V	
$V_{IL}$	On Input Logic LOW Voltage	$V_{IN} = 5.5 \text{ V}$				1.0		
I <sub>ON</sub>	On Input Leakage	$V_{ON} = V_{IN}$ or GND				1.0	μA	
I <sub>SWOFF</sub>	Off Switch Leakage	$V_{ON} = 0$ V, $V_{OUT} = 0$ V at $V_{IN} = 5.5$ V, $T_A = 85^{\circ}C$				1.0	μA	
		$V_{ON} = 0 \text{ V}, V_{OUT} = 0 \text{ V}$ $T_A = 85^{\circ}\text{C}$		10	100	nA		
	FLACE Cutant Lania Lan Valtana	V <sub>IN</sub> = 5.5 V, I <sub>SINK</sub> = 10 mA				0.2	.,	
	FLAGB Output Logic Low Voltage	$V_{IN} = 1.8 \text{ V}, I_{SINK} = 10$			0.3	V		
	FLAGB Output High Leakage Current	V <sub>IN</sub> = 5 V, Switch On			1.0	μÆ		
Protections	5							
I <sub>LIM</sub>	Current Limit	$V_{IN} = 3.3 \text{ V}, V_{OUT} = 2$	.0 V	200	300	400	m/	
		Shutdown Threshold		1,0	140			
	Thermal Shutdown	Return from Shutdown Hysteresis			130		°C	
				/	10			
$U_{VLO}$	Under-Voltage Lockout	V <sub>IN</sub> Increasing		1.5	1.6	1.7	V	
U <sub>VLOH</sub>	Under-Voltage Lockout Hysteresis				47		m\	
Dynamic C	haracteristics				,			
t <sub>ON</sub>	Turn-On Time	$R_L = 500 \ \Omega, \ C_L = 0.1 \ \mu F$			22		μs	
toff	Turn-Off Time	$R_L=500~\Omega,~C_L=0.1$	μF		20		μs	
t <sub>RISE</sub>	V <sub>OUT</sub> Rise Time	$R_L = 500 \Omega$ , $C_L = 0.1 \mu F$			13		μs	
t <sub>FALL</sub>	V <sub>OUT</sub> Fall Time	$R_L = 500 \Omega$ , $C_L = 0.1 \mu F$			117		μs	
t <sub>BLANK</sub>	Over-Current Blanking Time			5	10	20	ms	
	Short Circuit Response Time	$V_{IN} = V_{ON} = 3.3 \text{ V}, \text{ Me}$ Current Condition	oderate Over-		3		μs	
	· ·	$V_{IN} = V_{ON} = 3.3 \text{ V}, \text{ Ha}$		20		ns		

#### **Typical Performance Characteristics** 120 $\bigvee_{ON} = \bigvee_{IN}$ 110 SUPPLY CURRENT (uA) SUPPLY CURRENT (uA) V<sub>IN</sub> = 5.5V 90 80 70 60 80 10 35 T<sub>J</sub>, JUNCTION TEMPERATURE (°C) 3 SUPPLY VOLTAGE (V) **Quiescent Current vs. Input Voltage Quiescent Current vs. Temperature** Figure 4. Figure 5. SUPPLY CURRENT (uA) SUPPLY CURRENT (uA) 7.0 7.0 7.0 0.8 $V_{IN} = 5.5V$ V<sub>IN</sub> = 5.5V 0.4 V<sub>IN</sub> = 3.3V 10 35 T<sub>J</sub>, JUNCTION TEMPERATURE (°C) 85 -15 10 35 T., JUNCTION TEMPERATURE (°C) Figure 6. I<sub>SHUTDOWN</sub> Current vs. Temperature Figure 7. I<sub>SWITCH-OFF</sub> Current vs. Temperature 60 1.8 V<sub>IN</sub> = 3.3∨ 1.6 SUPPLY CURRENT (uA) 25 26 27 1.4 ON THRESHOLD (V) 1.2 1.0 0.8 0.6 0.2 0.0 40 3 3.5 4 4.5 V<sub>IN</sub>, INPUT VOLTAGE (V) 1.5 2.5 2 10 35 T<sub>.i</sub>, JUNCTION TEMPERATURE (°C) -40 Latch-off Current vs. Temperature Figure 9. Input Voltage vs. On Threshold Voltage Figure 8.





## **Description of Operation**

The FPF2172 is a current limited switch that protects systems and loads which can be damaged or disrupted by the application of high currents. The core of the device is a 0.125  $\Omega$  P-channel MOSFET and a controller capable of functioning over a wide input operating range of 1.8-5.5 V paired with a low forward voltage drop Schottky diode for reverse blocking. The controller protects against system malfunctions through current limiting, under-voltage lockout and thermal shutdown. The current limit is preset for 200 mA.

#### On/Off Control

The ON pin controls the state of the switch. Activating ON continuously holds the switch in the ON state so long as there is no under-voltage on VIN or a junction temperature in excess of 150°C. ON is active HI and has a low threshold making it capable of interfacing with low voltage signals. When the MOSFET is off, the Schottky diode acts as a barrier so that no reverse current can flow when Vout is greater than VIN.

#### **Fault Reporting**

Upon the detection of an over-current, an input undervoltage, or an over-temperature condition, the FLAGB signals the fault mode by activating LO. The FLAGB goes LO at the end of the blanking time and is latched LO and ON must be toggled to release it. FLAGB is an open-drain MOSFET which requires a pull-up resistor between VIN and FLAGB. During shutdown, the pull-down on FLAGB is disabled to reduce current draw from the supply.

#### **Current Limiting**

The current limit guarantees that the current through the switch doesn't exceed a maximum value while not limiting at less than a minimum value. The minimum current is 200 mA and the maximum current is 400 mA. The device has a blanking time of 10 ms, nominally, during which the switch will act as a constant current source. At the end of the blanking time, the switch will be turned-off and the FLAGB pin will activate to indicate that current limiting has occurred.

#### **Under-Voltage Lockout (UVLO)**

The under-voltage lockout turns-off the switch if the input voltage drops below the under-voltage lockout threshold. With the ON pin active the input voltage rising above the under-voltage lockout threshold will cause a controlled turn-on of the switch which limits current overshoots.

#### Thermal Shutdown

The thermal shutdown protects the die from internally or externally generated excessive temperatures. During an over-temperature condition the FLAGB is activated and the switch is turned-off. The switch automatically turns-on again if temperature of the die drops below the threshold temperature.

### **Applications Information**

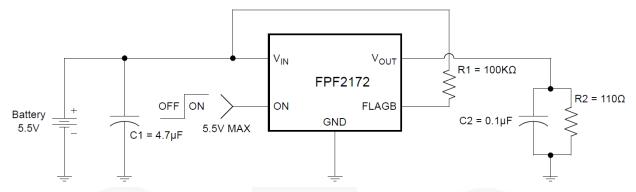


Figure 22. Typical Application

# **Input Capacitor**

To limit the voltage drop on the input supply caused by transient in-rush currents when the switch turns-on into a discharged load capacitor or a short-circuit, a capacitor needs to be placed between VIN and GND. A 4.7  $\mu F$  ceramic capacitor,  $C_{\text{IN}}$ , must be placed close to the VIN pin. A higher value of  $C_{\text{IN}}$  can be used to further reduce the voltage drop experienced as the switch is turned on into a large capacitive load.

#### **Output Capacitor**

A 0.1  $\mu F$  capacitor  $C_{OUT}$ , should be placed between  $V_{OUT}$  and GND. This capacitor will prevent parasitic board inductances from forcing  $V_{OUT}$  below GND when the switch turns-off.

#### **Power Dissipation**

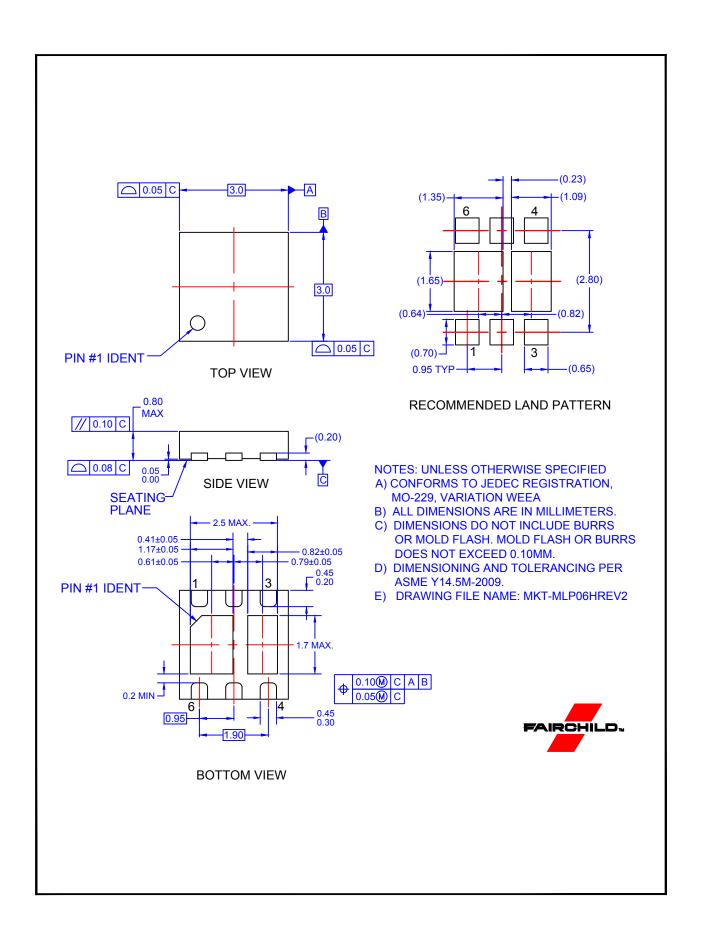
During normal operation as a switch, the power dissipation is small and has little effect on the operating temperature of the part. The parts with the higher current limits will dissipate the most power and that will only be typically:

$$P = I_{LIM} \times V_{DROP} = 0.4 \times 0.4 = 160 \text{mW}$$
 (1)

When using the part, attention must be given to the manual resetting of the part. Continuously resetting the part at a high duty cycle when a short on the output is present can cause the temperature of the part to increase. The junction temperature will only be allowed to increase to the thermal shutdown threshold. Once this temperature has been reached, toggling ON will not turn-on the switch until the junction temperature drops.

#### **Board Layout**

For best performance, all traces should be as short as possible. To be most effective, the input and output capacitors should be placed close to the device to minimize the effects that parasitic trace inductances may have on normal and short-circuit operation. Using wide traces for  $V_{\text{IN}}$ ,  $V_{\text{OUT}}$  and GND will help minimize parasitic electrical effects along with minimizing the case to ambient thermal impedance.



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